

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A sintered body, comprising a  $\text{SrRuO}_3$  conductive oxide sintered body containing an amount greater than 0.5mol% to and no greater than 1.2mol% of  $\text{Bi}_2\text{O}_3$  and having a relative density of 93% or more.

Claim 2 (previously presented): A conductive oxide sintered body according to claim 1, wherein the sintered body has a resistivity of  $500 \mu \Omega\text{cm}$  or less.

Claim 3 (previously presented): A conductive oxide sintered body according to claim 1, wherein the sintered body has a resistivity of  $300 \mu \Omega\text{cm}$  or less.

Claims 4-5 (canceled).

Claim 6 (currently amended): A sputtering target, comprising a  $\text{SrRuO}_3$  conductive oxide sintered body containing an amount greater than 0.5mol% to and no greater than 1.2mol% of  $\text{Bi}_2\text{O}_3$  and having a relative density of 93% or more.

Claim 7 (previously presented): A sputtering target according to claim 6, wherein the sputtering target has a resistivity of  $500 \mu \Omega\text{cm}$  or less.

Claim 8 (previously presented): A sputtering target according to claim 6, wherein the sputtering target has a resistivity of  $300 \mu \Omega \text{cm}$  or less.

Claims 9-10 (canceled).

Claim 11 (currently amended): A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from said sintered body, comprising the step of adding an amount greater than 0.5mol% to and no greater than 1.2mol% of  $\text{Bi}_2\text{O}_3$  as a sintering auxiliary upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.

Claims 12-14 (canceled).

Claim 15 (previously presented): A method according to claim 11, further comprising the step of sintering at a temperature of 1400 to 1700°C upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.

Claim 16 (new): A method according to claim 15, wherein said temperature during said sintering is 1600 to 1700°C.

Claim 17 (new): A method according to claim 15, further comprising the step of CIP (cold isostatic pressing) molding before said sintering step upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.

Claim 18 (new): A method according to claim 17, wherein said CIP molding is at a pressure of 1500kg/cm<sup>2</sup>.

Claim 19 (new): A method according to claim 15, wherein said sintered body is set inside a vented alumina container during said sintering step.